

Silicon NPN Power Transistors

BD233 BD235 BD237

DESCRIPTION

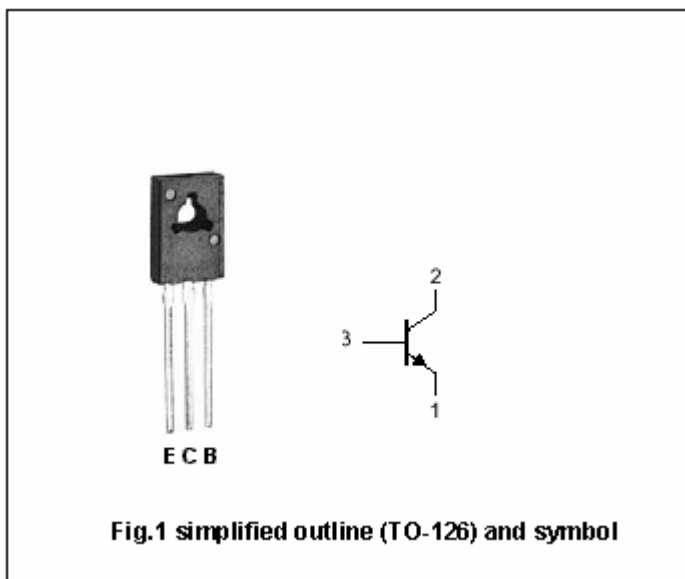
- With TO-126 package
- Complement to type BD234 /236 /238

APPLICATIONS

- For medium power linear and switching applications

PINNING

PIN	DESCRIPTION
1	Emitter
2	Collector;connected to mounting base
3	Base



Absolute maximum ratings (Ta=25°C)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V _{CBO}	Collector-base voltage	BD233	45	V
		BD235	60	
		BD237	100	
V _{CEO}	Collector-emitter voltage	BD233	45	V
		BD235	60	
		BD237	80	
V _{EBO}	Emitter -base voltage	Open collector	5	V
I _C	Collector current (DC)		2	A
I _{CM}	Collector current-Peak		6	A
P _C	Collector power dissipation	T _C =25°C	25	W
T _j	Junction temperature		150	°C
T _{stg}	Storage temperature		-65~150	°C

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CHARACTERISTICS

T_j=25°C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V _{CEsat}	Collector-emitter saturation voltage	I _C =1A; I _B =0.1A			0.6	V
V _{BE}	Base-emitter on voltage	I _C =1A; V _{CE} =2V			1.3	V
V _{CEO(SUS)}	Collector-emitter sustaining voltage	BD233	I _C =0.1A; I _B =0	45		V
		BD235		60		
		BD237		80		
I _{CBO}	Collector cut-off current	BD233	V _{CB} =45V; I _E =0		100	μA
		BD235	V _{CB} =60V; I _E =0			
		BD237	V _{CB} =100V; I _E =0			
I _{EBO}	Emitter cut-off current	V _{EB} =5V; I _C =0			1	mA
h _{FE-1}	DC current gain	I _C =150mA; V _{CE} =2V	40			
h _{FE-2}	DC current gain	I _C =1A; V _{CE} =2V	25			
f _T	Transition frequency	I _C =250mA; V _{CE} =10V	3			MHz

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PACKAGE OUTLINE

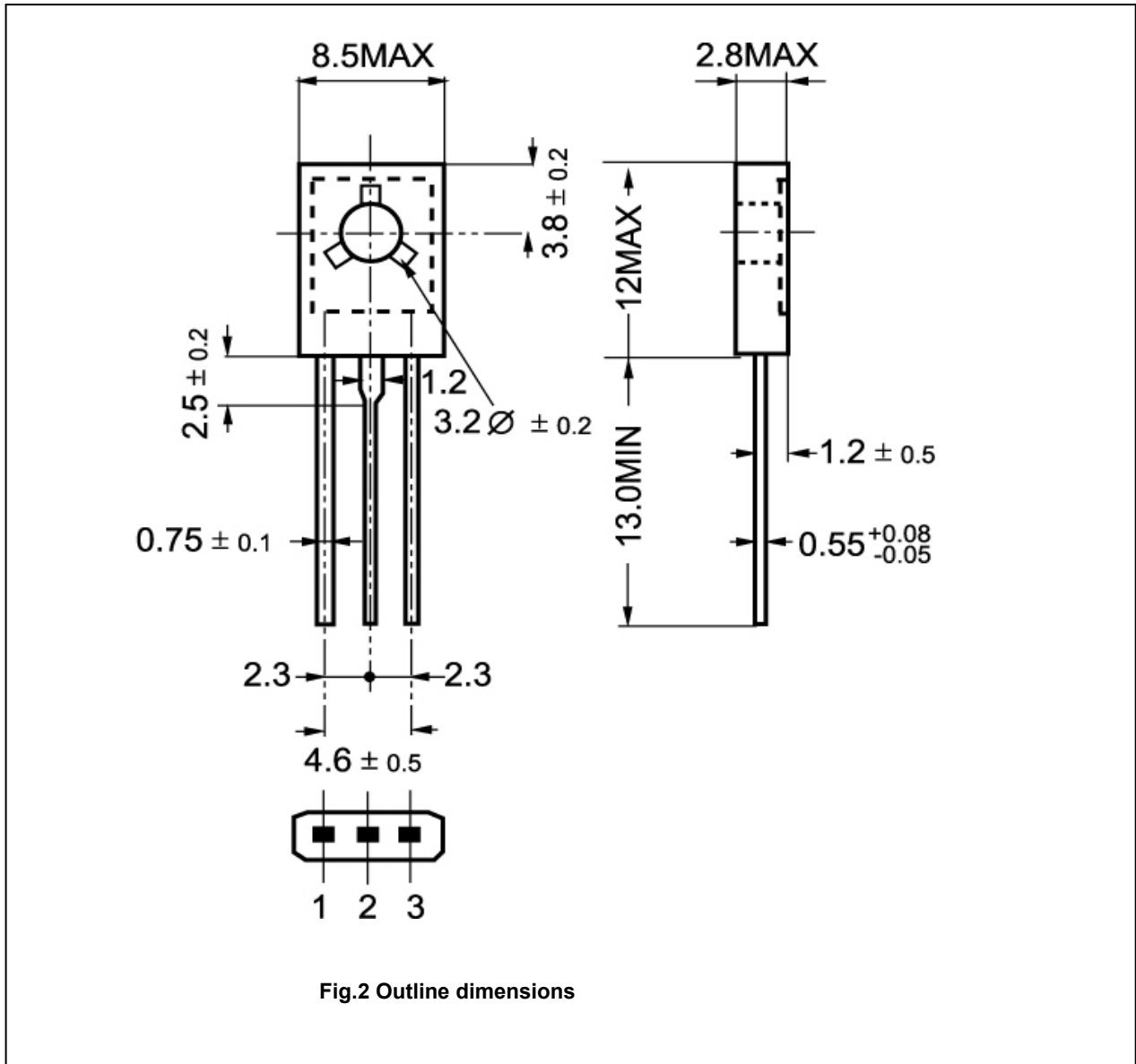


Fig.2 Outline dimensions